

R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

For a detailed explanation of implementing these values in P-SPIICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPIICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



| R-C VALUES FOR TANK CONFIGURATION | | | |
|--|------------|------------|------|
| Thermal Resistance (°C/W) | | | |
| Junction to | Ambient | Case | Foot |
| RT1 | 9.3175 | 467.3319 m | N/A |
| RT2 | 1.7290 | 793.1223 m | N/A |
| RT3 | 6.4796 | 656.8746 m | N/A |
| RT4 | 47.4739 | 82.6712 m | N/A |
| Thermal Capacitance (Joules/°C) | | | |
| Junction to | Ambient | Case | Foot |
| CT1 | 303.2258 m | 3.2992 m | N/A |
| CT2 | 3.0667 m | 20.4434 m | N/A |
| CT3 | 52.0372 m | 23.0380 m | N/A |
| CT4 | 1.3756 | 2.5581 m | N/A |

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

| Thermal Resistance (°C/W) | | | |
|---------------------------------|------------|------------|------|
| Junction to | Ambient | Case | Foot |
| RF1 | 4.0535 | 422.3661 m | N/A |
| RF2 | 10.7203 | 598.8721 m | N/A |
| RF3 | 18.7708 | 970.7546 m | N/A |
| RF4 | 31.4554 | 8.0072 m | N/A |
| Thermal Capacitance (Joules/°C) | | | |
| Junction to | Ambient | Case | Foot |
| CF1 | 9.7862 m | 1.3980 m | N/A |
| CF2 | 68.9511 m | 2.9248 m | N/A |
| CF3 | 565.2801 m | 11.2432 m | N/A |
| CF4 | 1.5967 | 108.3211 m | N/A |

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

